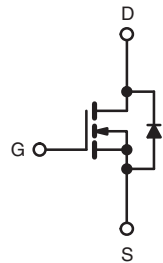
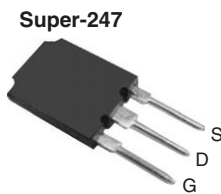


## Power MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	600	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10$ V	0.12
$Q_g$ (Max.) (nC)	320	
$Q_{gs}$ (nC)	85	
$Q_{gd}$ (nC)	160	
Configuration	Single	



N-Channel MOSFET

### FEATURES

- Superfast Body Diode Eliminates the Need for External Diodes in ZVS Applications
- Lower Gate Charge Results in Simple Drive Requirements
- Enhanced  $dV/dt$  Capabilities Offer Improved Ruggedness
- Higher Gate Voltage Threshold Offers Improved Noise Immunity
- Compliant to RoHS Directive 2002/95/EC



**RoHS\***  
COMPLIANT

### APPLICATIONS

- Zero Voltage Switching SMPS
- Telecom and Server Power Supplies
- Uninterruptible Power Supplies
- Motor Control applications

ORDERING INFORMATION	
Package	Super-247
Lead (Pb)-free	IRFPS38N60LPbF
	SiHFPS38N60L-E3
SnPb	IRFPS38N60L
	SiHFPS38N60L

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ , unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	$V_{DS}$	600	V	
Gate-Source Voltage	$V_{GS}$	$\pm 30$		
Continuous Drain Current	$V_{GS}$ at 10 V	$T_C = 25^\circ\text{C}$	A	
		$T_C = 100^\circ\text{C}$		
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	150		
Linear Derating Factor		4.3	W/ $^\circ\text{C}$	
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	680	mJ	
Repetitive Avalanche Current <sup>a</sup>	$I_{AR}$	38	A	
Repetitive Avalanche Energy <sup>a</sup>	$E_{AR}$	54	mJ	
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	$P_D$	540	W
Peak Diode Recovery $dV/dt^c$		$dV/dt$	19	V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to + 150	$^\circ\text{C}$	
Soldering Recommendations (Peak Temperature)	for 10 s	300 <sup>d</sup>		
Mounting Torque	6-32 or M3 screw		10	lbf · in
			1.1	N · m


### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 12).
- Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.91$  mH,  $R_g = 25 \Omega$ ,  $I_{AS} = 38$  A,  $dV/dt = 13$  V/ns (see fig. 14a).
- $I_{SD} \leq 38$  A,  $dI/dt \leq 630$  A/ $\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150^\circ\text{C}$ .
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	40	°C/W
Case-to-Sink, Flat, Greased Surface	$R_{thCS}$	0.24	-	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.22	

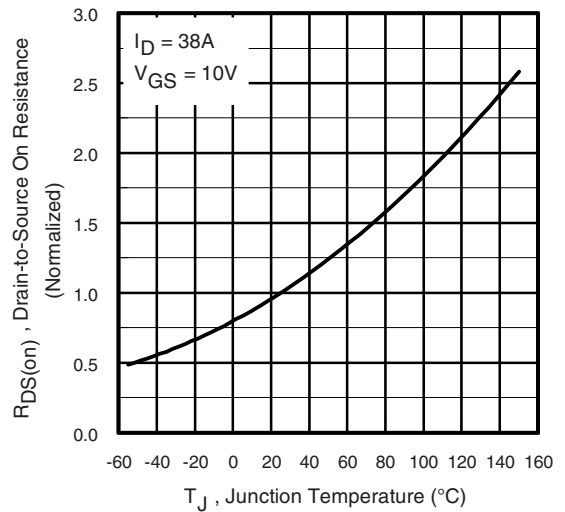
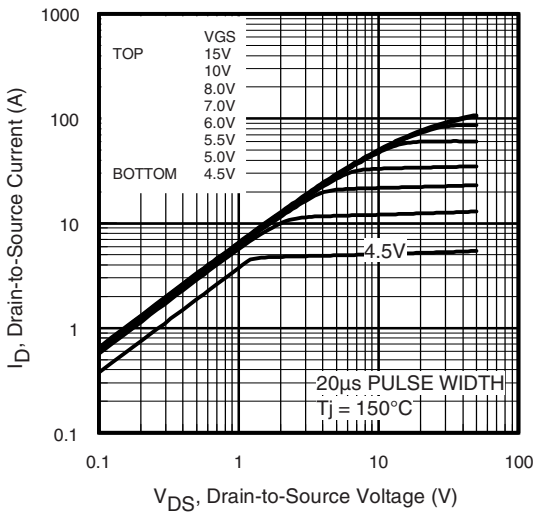
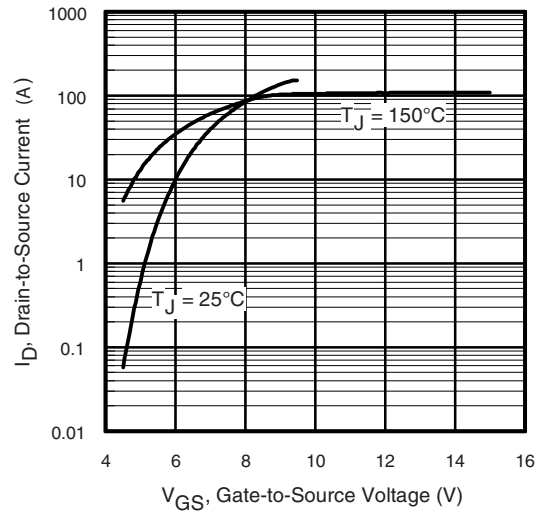
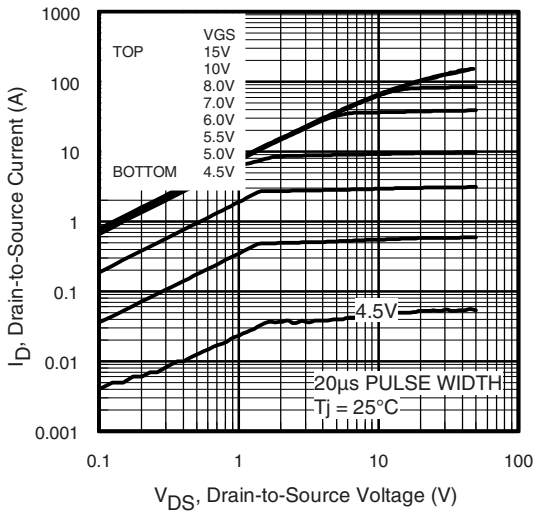
## SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	600	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$	-	410	-	mV/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3.0	-	5.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30\text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 600\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	50	$\mu\text{A}$
		$V_{DS} = 480\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$	-	-	2.0	mA
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 23\text{ A}^b$	-	0.12	0.15	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}$ , $I_D = 23\text{ A}^b$	20	-	-	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1.0\text{ MHz}$ , see fig. 5	-	7990	-	pF
Output Capacitance	$C_{oss}$		-	740	-	
Reverse Transfer Capacitance	$C_{rss}$		-	72	-	
Effective Output Capacitance	$C_{oss\text{ eff.}}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 0\text{ V to } 480\text{ V}^c$	-	350	-	pF
Effective Output Capacitance (Energy Related)	$C_{oss\text{ eff. (ER)}}$		-	260	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$ , $I_D = 38\text{ A}$ , $V_{DS} = 480\text{ V}$ see fig. 7 and 15 <sup>b</sup>	-	-	320	nC
Gate-Source Charge	$Q_{gs}$		-	-	85	
Gate-Drain Charge	$Q_{gd}$		-	-	160	
Gate Resistance	$R_G$	$f = 1\text{ MHz}$ , open drain	-	1.2	-	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300\text{ V}$ , $I_D = 38\text{ A}$ , $R_G = 4.3\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ , see fig. 11a and 11b <sup>b</sup>	-	44	-	ns
Rise Time	$t_r$		-	130	-	
Turn-Off Delay Time	$t_{d(off)}$		-	92	-	
Fall Time	$t_f$		-	69	-	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	38	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$		-	-	150	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_S = 38\text{ A}$ , $V_{GS} = 0\text{ V}^b$	-	-	1.5	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_F = 38\text{ A}$	-	170	250	ns
		$T_J = 125\text{ }^\circ\text{C}$ , $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	420	630	
Body Diode Reverse Recovery Charge	$Q_{rr}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_F = 38\text{ A}$ , $V_{GS} = 0\text{ V}^b$	-	830	1240	nC
		$T_J = 125\text{ }^\circ\text{C}$ , $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	2600	3900	
Reverse Recovery Time	$I_{RRM}$	$T_J = 25\text{ }^\circ\text{C}$	-	9.1	14	A
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )				

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 12).
- Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- $C_{oss\text{ eff.}}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DS}$ .  
 $C_{oss\text{ eff. (ER)}}$  is a fixed capacitance that stores the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DS}$ .

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



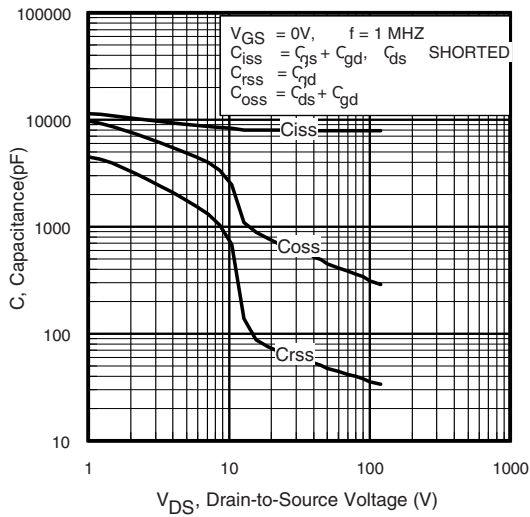


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

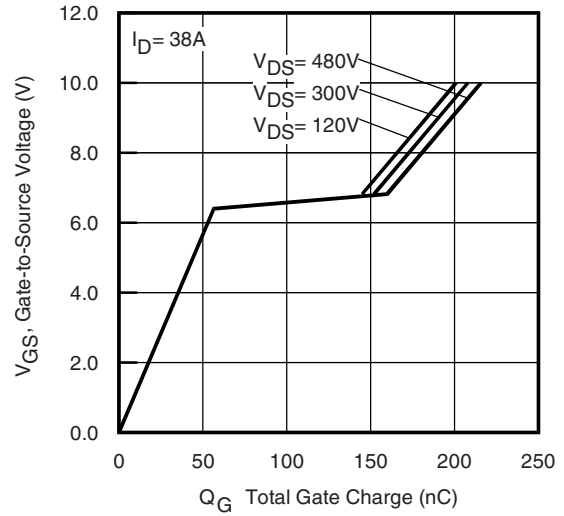


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

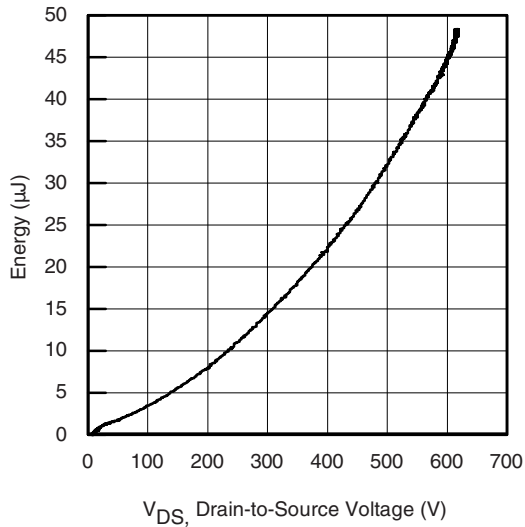


Fig. 6 - Typical Output Capacitance Stored Energy vs.  $V_{DS}$

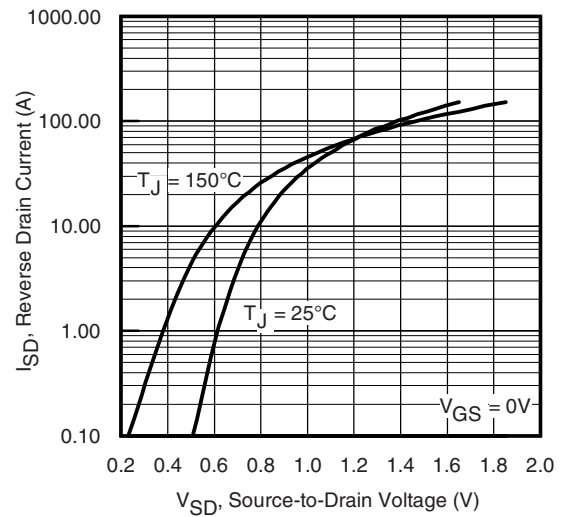
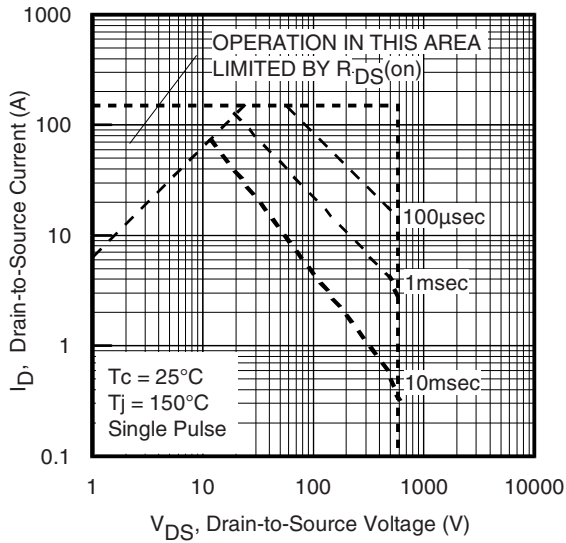
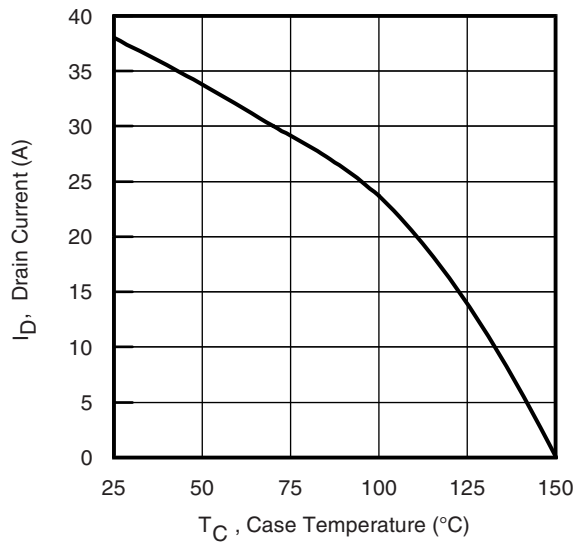


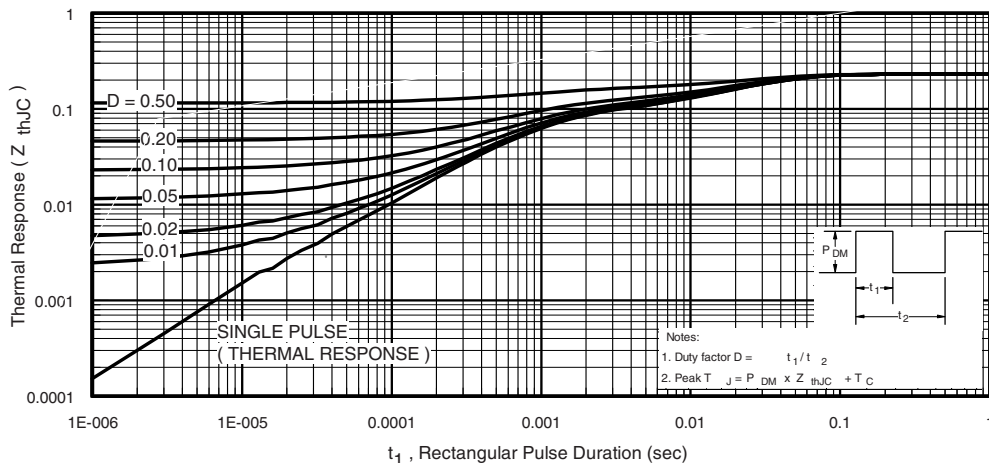
Fig. 8 - Typical Source-Drain Diode Forward Voltage



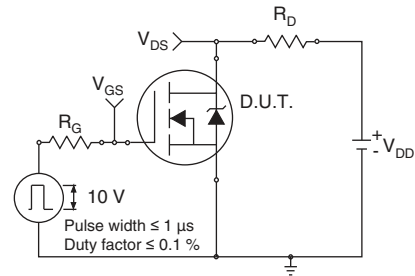
**Fig. 9 - Maximum Safe Operating Area**



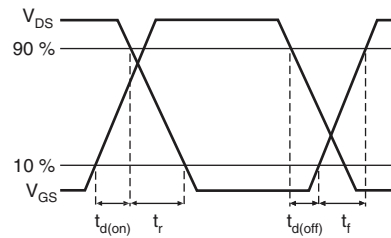
**Fig. 10 - Maximum Drain Current vs. Case Temperature**



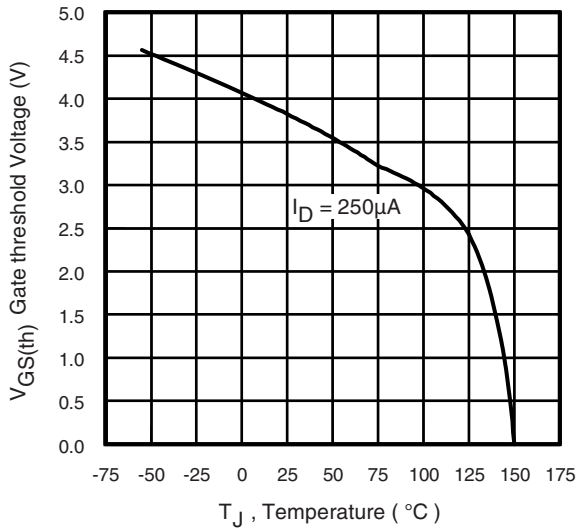
**Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**



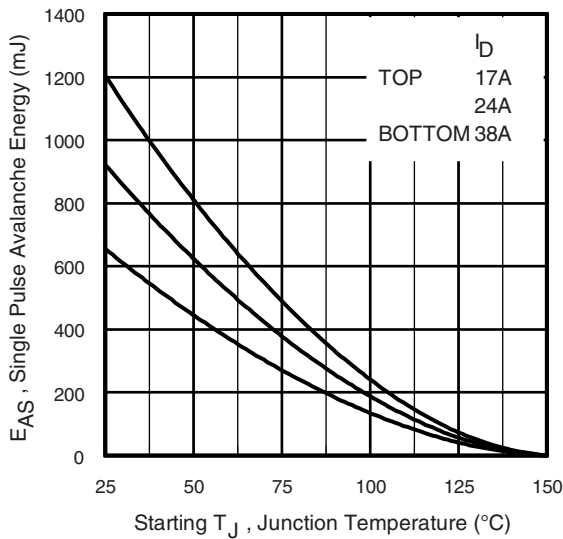
**Fig. 11a - Switching Time Test Circuit**



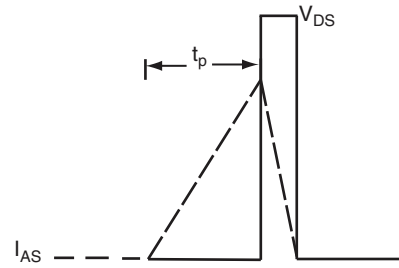
**Fig. 11b - Switching Time Waveforms**



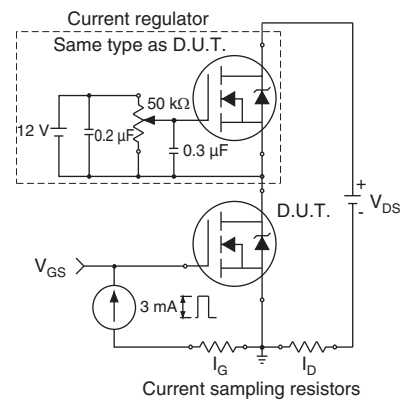
**Fig. 13 - Threshold Voltage vs. Temperature**



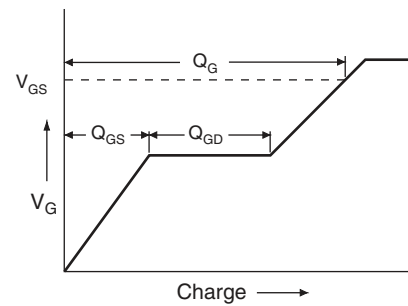
**Fig. 14a - Maximum Avalanche Energy vs. Drain Current**



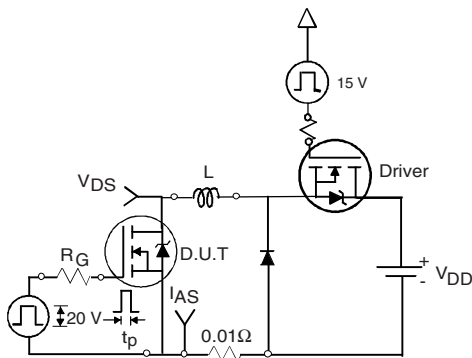
**Fig. 14c - Unclamped Inductive Waveforms**



**Fig. 15a - Basic Gate Charge Waveform**



**Fig. 15b - Gate Charge Test Circuit**



**Fig. 14b - Unclamped Inductive Test Circuit**

### Peak Diode Recovery dV/dt Test Circuit



**Note**

a.  $V_{GS} = 5\text{ V}$  for logic level devices

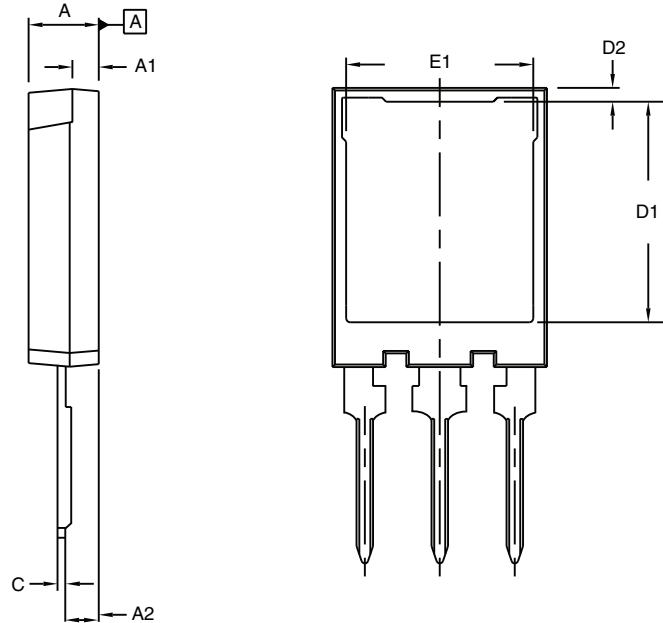
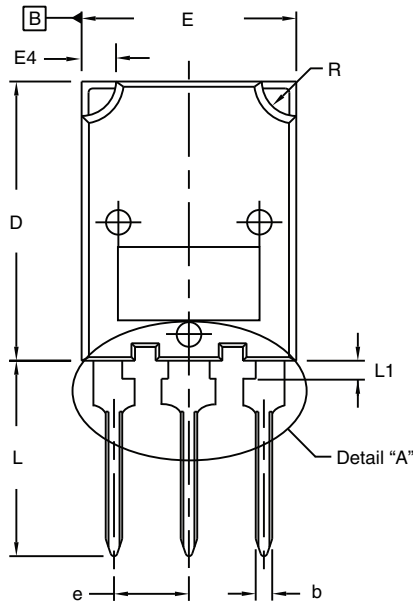
**Fig. 16 - For N-Channel**

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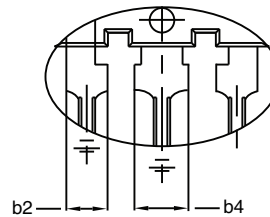


# TO-274AA (High Voltage)

## VERSION 1: FACILITY CODE = Y



⊕ 0.10 (0.25) ⊖ B A ⊕



Detail "A"  
Scale: 2:1

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.70	5.30	0.185	0.209
A1	1.50	2.50	0.059	0.098
A2	2.25	2.65	0.089	0.104
b	1.30	1.60	0.051	0.063
b2	1.80	2.20	0.071	0.087
b4	3.00	3.25	0.118	0.128
c <sup>(1)</sup>	0.38	0.89	0.015	0.035
D	19.80	20.80	0.780	0.819

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	15.50	16.10	0.610	0.634
D2	0.70	1.30	0.028	0.051
E	15.10	16.10	0.594	0.634
E1	13.30	13.90	0.524	0.547
e	5.45 BSC		0.215 BSC	
L	13.70	14.70	0.539	0.579
L1	1.00	1.60	0.039	0.063
R	2.00	3.00	0.079	0.118

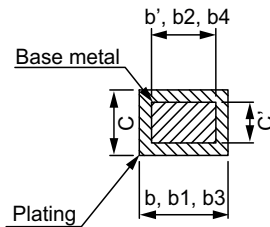
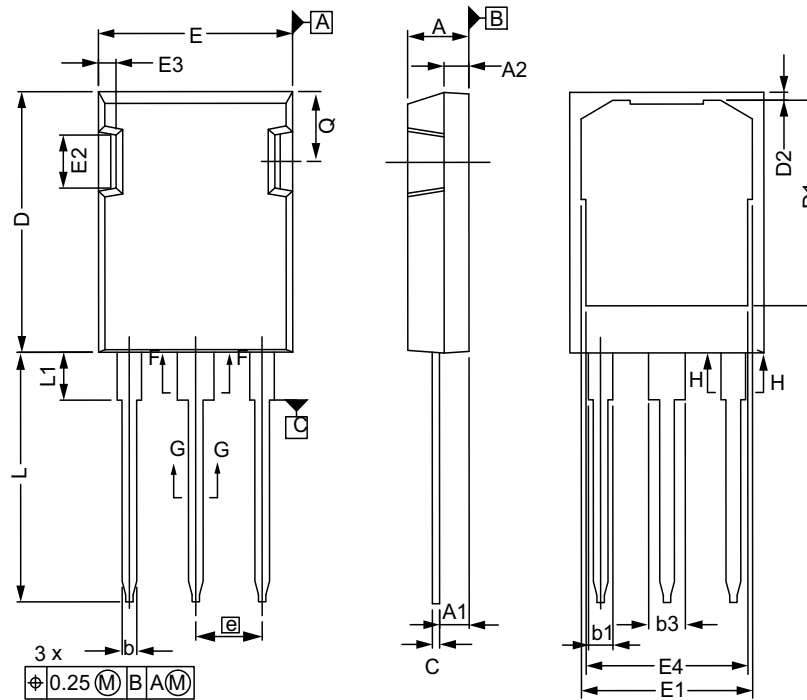
### Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outer extremes of the plastic body
- Outline conforms to JEDEC® outline to TO-274AA
- (1) Dimension measured at tip of lead





VERSION 2: FACILITY CODE = N



SECTION "F-F", "G-G" AND "H-H"  
SCALE: NONE

MILLIMETERS		
DIM.	MIN.	MAX.
A	4.83	5.21
A1	2.29	2.54
A2	1.91	2.16
b'	1.07	1.28
b	1.07	1.33
b1	1.91	2.41
b2	1.91	2.16
b3	2.87	3.38
b4	2.87	3.13
c'	0.55	0.65
c	0.55	0.68
D	20.80	21.10

MILLIMETERS		
DIM.	MIN.	MAX.
D1	16.25	17.65
D2	0.50	0.80
E	15.75	16.13
E1	13.10	14.15
E2	3.68	5.10
E3	1.00	1.90
E4	12.38	13.43
e	5.44 BSC	
N	3	
L	19.81	20.32
L1	3.70	4.00
Q	5.49	6.00

ECN: E20-0538-Rev. C, 19-Oct-2020  
DWG: 5975

Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- Outline conforms to JEDEC® outline to TO-274AD
- Dimensions are measured in mm, angles are in degree
- Metal surfaces are tin plated, except area of cut



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